

# SKM600GB126D



**SEMITRANS® 3**

## Trench IGBT Modules

### SKM600GB126D

#### Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability, self limiting to  $6 \times I_C$
- UL recognized, file no. E63532

#### Typical Applications\*

- AC inverter drives
- UPS
- Electronic welders

#### Remarks

- $I_{DC} \leq 500A$  for  $T_{Terminal} = 100\text{ }^\circ\text{C}$



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25\text{ }^\circ\text{C}$	1200	V	
$I_C$	$T_j = 150\text{ }^\circ\text{C}$	$T_c = 25\text{ }^\circ\text{C}$	660	A
		$T_c = 80\text{ }^\circ\text{C}$	461	A
$I_{Cnom}$		400	A	
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	800	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 600\text{ V}$	$T_j = 125\text{ }^\circ\text{C}$	10	$\mu\text{s}$
	$V_{GE} \leq 15\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
$T_j$		-40 ... 150	$^\circ\text{C}$	
<b>Inverse diode</b>				
$I_F$	$T_j = 150\text{ }^\circ\text{C}$	$T_c = 25\text{ }^\circ\text{C}$	490	A
		$T_c = 80\text{ }^\circ\text{C}$	337	A
$I_{Fnom}$		400	A	
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	800	A	
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25\text{ }^\circ\text{C}$	3312	A	
$T_j$		-40 ... 150	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$		500	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V	

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 400\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ }^\circ\text{C}$	1.70	2.12	V
		$T_j = 125\text{ }^\circ\text{C}$	2.02	2.46	V
$V_{CE0}$	chipelevel	$T_j = 25\text{ }^\circ\text{C}$	1	1.2	V
		$T_j = 125\text{ }^\circ\text{C}$	0.9	1.1	V
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ }^\circ\text{C}$	1.75	2.3	m $\Omega$
		$T_j = 125\text{ }^\circ\text{C}$	2.8	3.4	m $\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 16\text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25\text{ }^\circ\text{C}$		5	mA
		$T_j = 125\text{ }^\circ\text{C}$			mA
$C_{ies}$	$V_{CE} = 25\text{ V}$	$f = 1\text{ MHz}$	28.8		nF
$C_{oes}$	$V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	1.51		nF
$C_{res}$		$f = 1\text{ MHz}$	1.31		nF
$Q_G$	$V_{GE} = -8\text{ V} \dots +20\text{ V}$		3600		nC
$R_{Gint}$	$T_j = 25\text{ }^\circ\text{C}$		1.9		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 400\text{ A}$	$T_j = 125\text{ }^\circ\text{C}$	290		ns
$t_r$	$V_{GE} = +15/-15\text{ V}$	$T_j = 125\text{ }^\circ\text{C}$	60		ns
$E_{on}$	$R_{Gon} = 2\text{ }^\circ\Omega$	$T_j = 125\text{ }^\circ\text{C}$	39		mJ
$t_{d(off)}$	$R_{Goff} = 2\text{ }^\circ\Omega$	$T_j = 125\text{ }^\circ\text{C}$	670		ns
$t_f$		$T_j = 125\text{ }^\circ\text{C}$	80		ns
$E_{off}$		$T_j = 125\text{ }^\circ\text{C}$	64		mJ
$R_{th(j-c)}$	per IGBT			0.055	K/W



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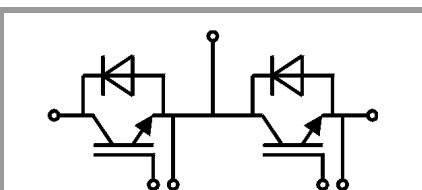
#### Typical Applications\*

- AC inverter drives
- UPS
- Electronic welders

#### Remarks

- $I_{DC} \leq 500A$  for  $T_{Terminal} = 100\text{ °C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{EC}$	$I_F = 400\text{ A}$ $V_{GE} = 0\text{ V}$ chipllevel	$T_j = 25\text{ °C}$		1.60	1.80	V
		$T_j = 125\text{ °C}$		1.60	1.80	V
$V_{F0}$	chipllevel	$T_j = 25\text{ °C}$		1	1.1	V
		$T_j = 125\text{ °C}$		0.8	0.9	V
$r_F$	chipllevel	$T_j = 25\text{ °C}$		1.50	1.75	mΩ
		$T_j = 125\text{ °C}$		2.00	2.3	mΩ
$I_{RRM}$	$I_F = 400\text{ A}$	$T_j = 125\text{ °C}$		475		A
$Q_{rr}$	$di/dt_{off} = 7600\text{ A}/\mu\text{s}$	$T_j = 125\text{ °C}$		96		μC
$E_{rr}$	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 125\text{ °C}$		41		mJ
$R_{th(j-c)}$	per diode				0.125	K/W
<b>Module</b>						
$L_{CE}$				15		nH
$R_{CC'+EE'}$	terminal-chip	$T_C = 25\text{ °C}$		0.35		mΩ
		$T_C = 125\text{ °C}$		0.5		mΩ
$R_{th(c-s)}$	per module			0.02	0.038	K/W
$M_s$	to heat sink M6		3		5	Nm
$M_t$		to terminals M6	2.5		5	Nm
						Nm
$w$					325	g



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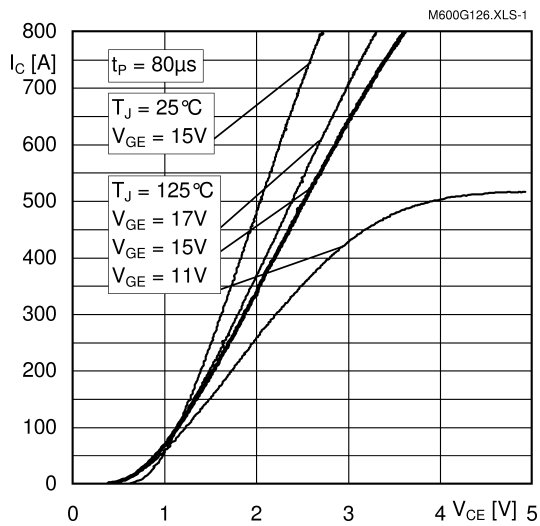


Fig. 1: Typ. output characteristic, inclusive  $R_{CC+EE}$

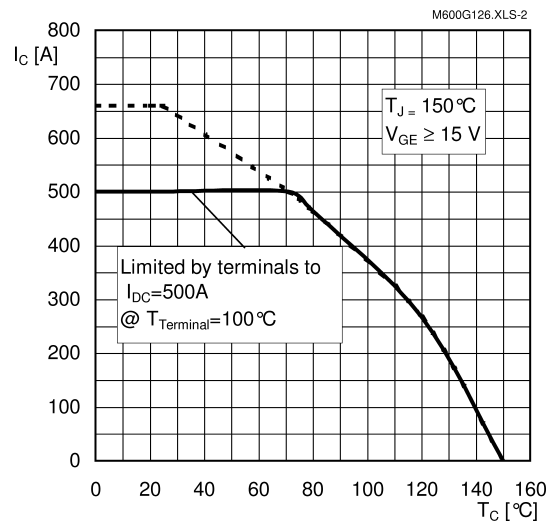


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

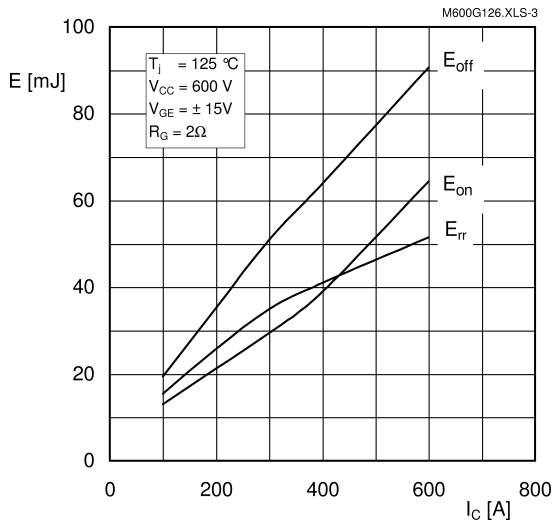


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

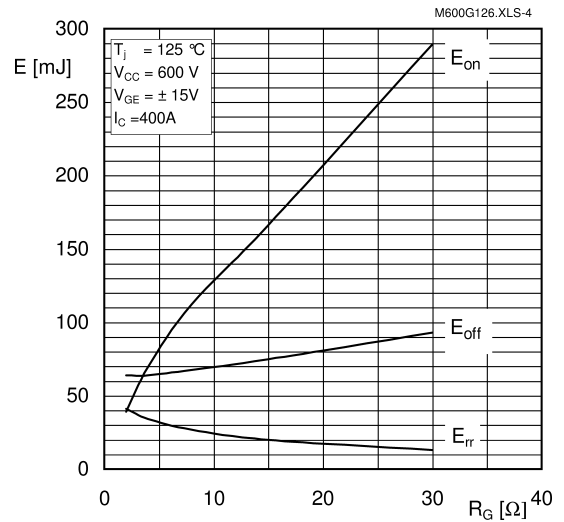


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

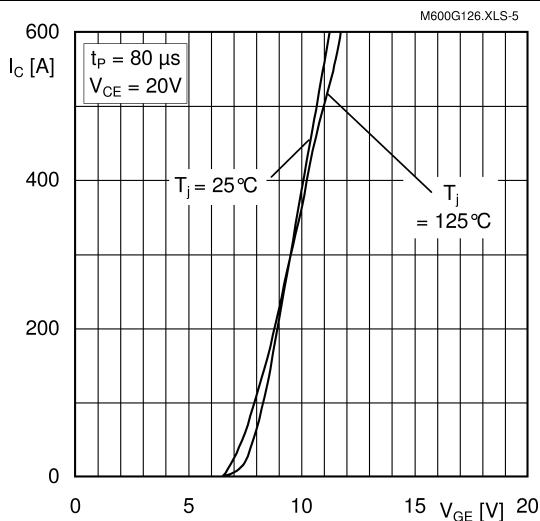


Fig. 5: Typ. transfer characteristic

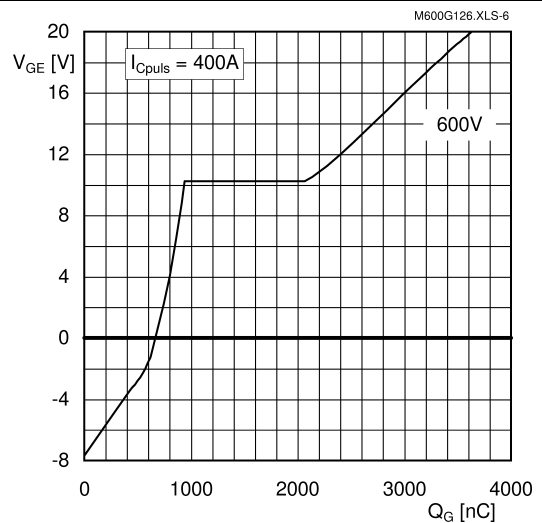


Fig. 6: Typ. gate charge characteristic

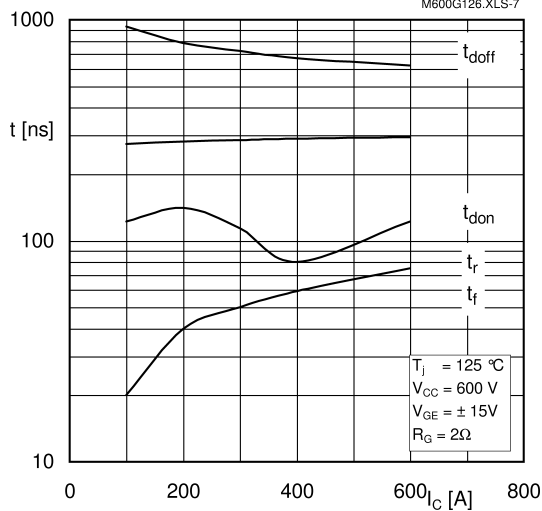


Fig. 7: Typ. switching times vs.  $I_C$

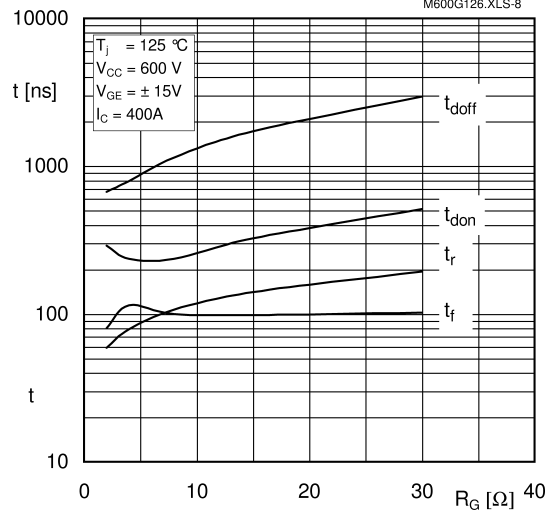


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

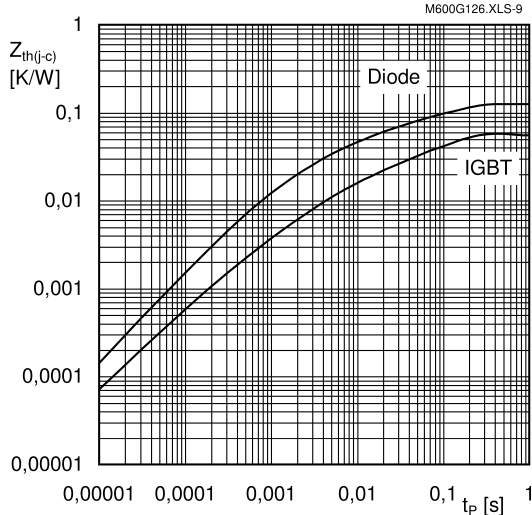


Fig. 9: Transient thermal impedance

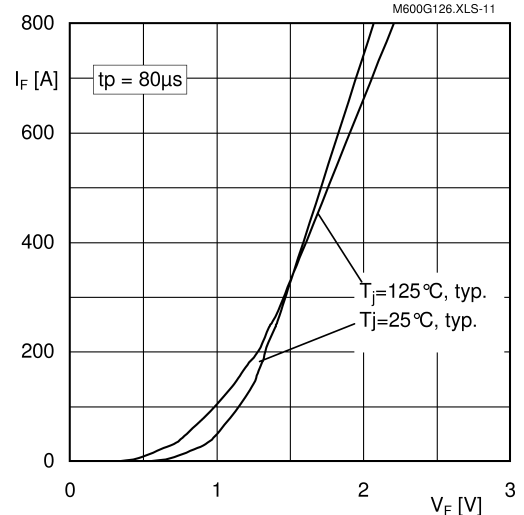


Fig. 10: Typ. CAL diode forward charact., incl.  $R_{CC+EE'}$

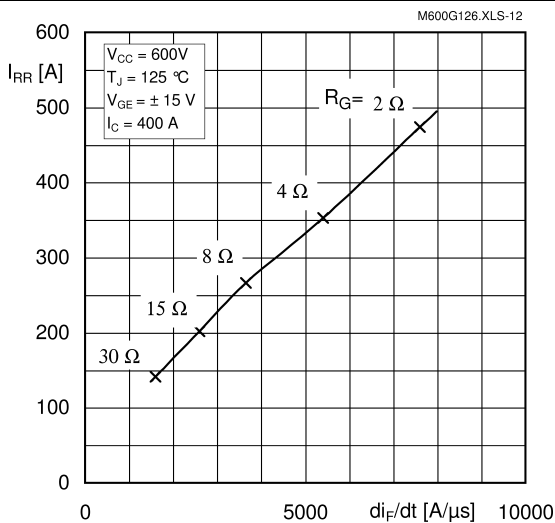


Fig. 11: Typ. CAL diode peak reverse recovery current

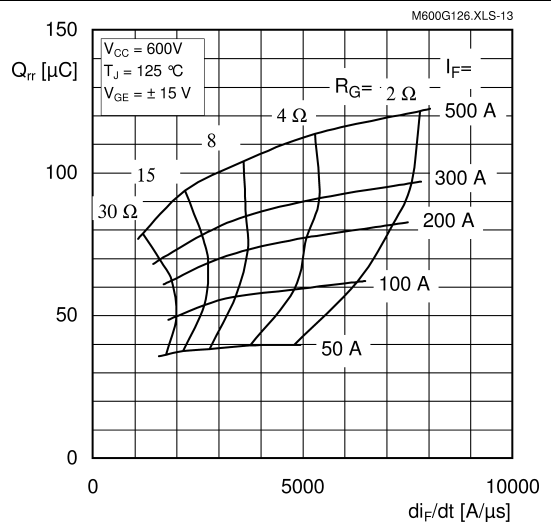


Fig. 12: Typ. CAL diode peak reverse recovery charge

